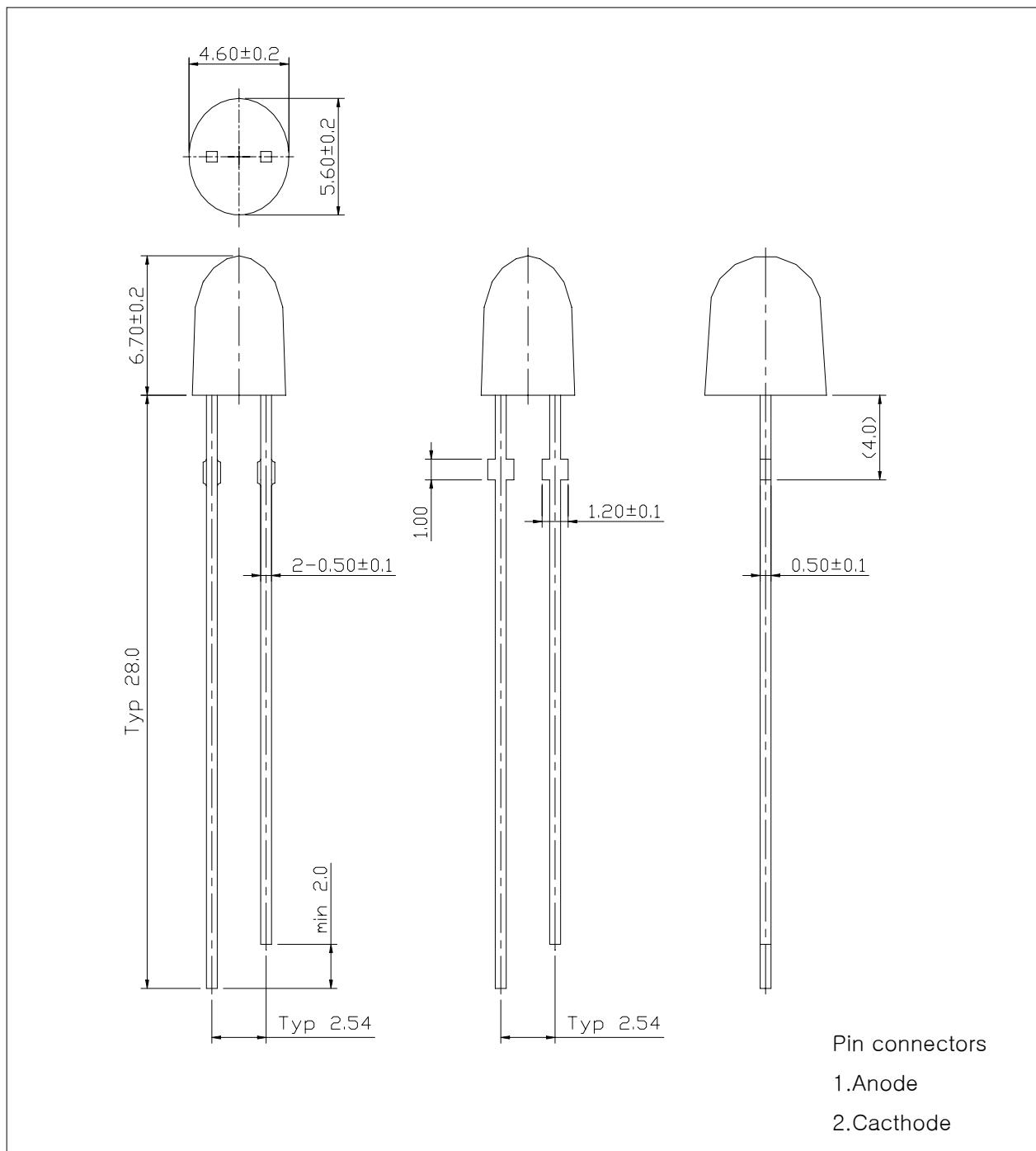


■ Features

- Colored diffusion lens type
- 5.6mm X 4.6mm Oval type
- High luminosity

■ Outline dimensions

(unit : mm)



Pin connectors
1. Anode
2. Cathode

High Brightness LED Lamp
■ Absolute Maximum Ratings

(Ta=25 °C)

Characteristic	Symbol	Ratings	Unit
Power dissipation	P _D	85	mW
Forward Current	I _F	30	mA
* ¹ Peak Forward Current	I _{FP}	100	mA
Reverse Voltage	V _R	5	V
Operating Temperature	T _{opr}	-30 ~ +85	°C
Storage Temperature	T _{stg}	-40 ~ +100	°C
* ² Soldering Temperature	T _{sol}	260°C for 3 seconds	

*1.Duty ratio 1/10, Pulse Width 10msec

*2.Keep the distance more than 2.0mm from PCB to the bottom of LED package

■ Electrical – Optical Characteristics

(Ta=25 °C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit	
Forward Voltage	V _F	I _F = 20Ma	-	2.0	2.7	V	
Dominant Wavelength	λ _d	I _F = 20Ma	-	624	-	nm	
Spectrum Bandwidth	Δλ	I _F = 20Ma	-	25	-	nm	
Reverse Current	I _R	V _R =5V	-	-	10	Ua	
* ³ Half Angle	θ1/2	I _F = 20mA	x	-	±17	-	deg
			y	-	±34	-	deg

*3. θ1/2 is the off-axis angle where the luminous intensity is 1/2 the peak intensity

■ Luminous intensity ranks

(Ta=25°C)

Iv RANK	Test Condition	Min.	Typ.	Max.	Unit
M	I _F = 20mA	420	–	600	mcd
N		600	–	850	
O		850	–	1200	
P		1200	–	1700	

* Luminous intensity is tested at a current pulse duration of 25 ms and an accuracy of ±11%.

Intensity Measured : 0.01sr(CIE. LED_B)

■ Precautions On LED using

- * To avoid optical difference, Please do not mix differently-ranked product.

■ Characteristic Diagrams

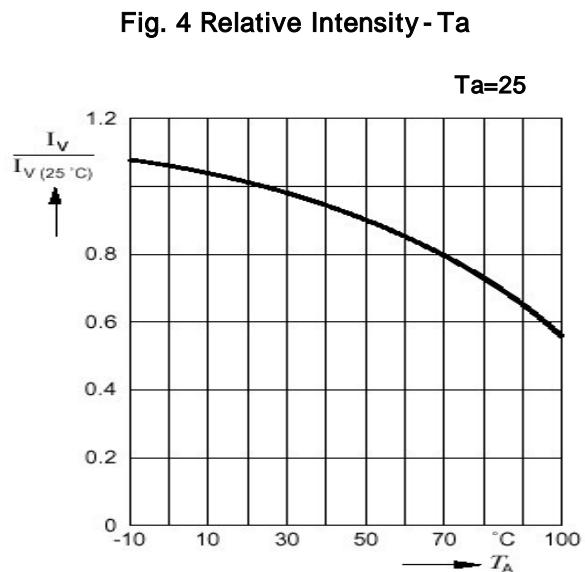
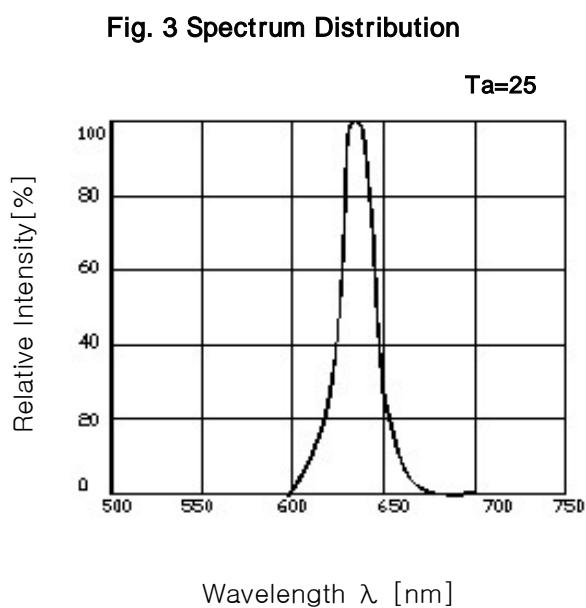
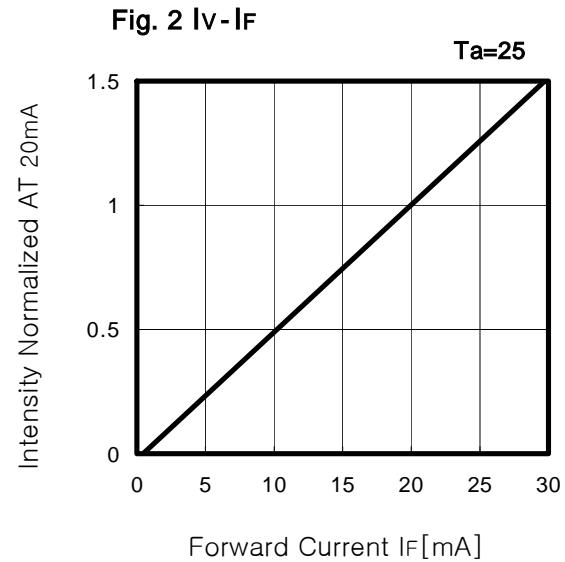
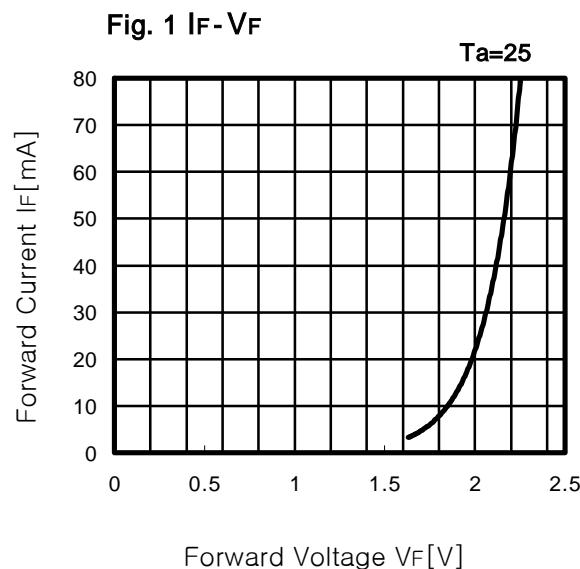
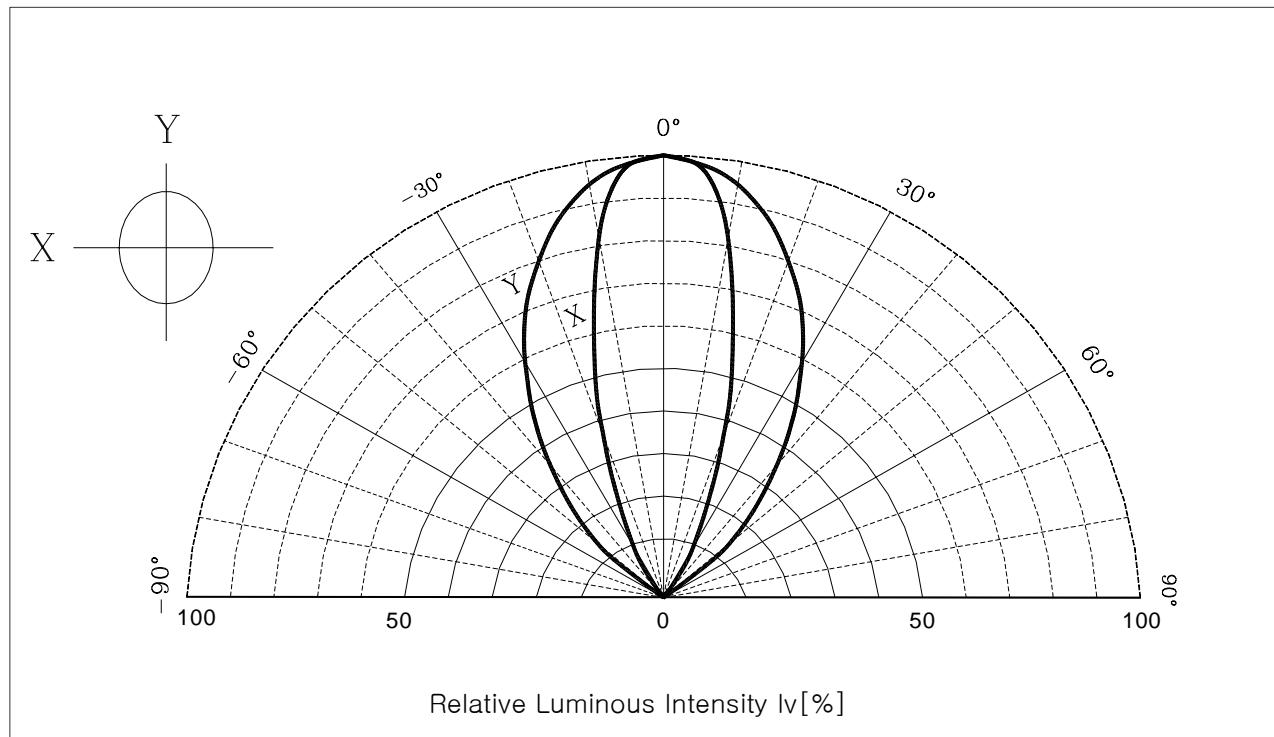


Fig. 5 Radiation Diagram

■ Revision history sheet

Spec NO.			
Title	Specification for Approval		
Times	Date	Summary of revision	Remarks
1	2001. 07. 15	신규제정	
2	2003. 02. 26	Format 변경	
3	2004. 06. 03	Iv Rank 변경	